## Dale Gleason

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## Contact Resistance Mechanisms

## Agilent Technologies

Innovating the HP Way



- Understand predictor influence on contact resistance
- Understand probe contact area

For Application to Probe Design and Processes

# Discussion

- Large variation may be present in contact resistance data.
- Some predictors difficult to measure well.
- If there is little or no correlation of contact resistance to predictors then contamination can be considered sole or primary issue.
- Contamination from three sources:
  - Present on wafer.
  - Present on clean surface.
  - Current produced film or oxide on probe.

# Contact Resistance Variable Gnarl



## Resistance Factors

## Probe Card

- Tip Diameter
- Planarity
- Tier
- Probe Force

## Probing

- Scrub Length
- Scrub Depth
- Scrub Width
- Scrub Area

## Tools Set

- EG4090 Prober
- API waferWoRx scrub analyzer
- Hewlett-Packard F330 Tester
- API PRVII probe card analyzer

## Test Wafer



- 8 inch bonding test wafer with 342 die at 352 pads each.
- Daisy-chained aluminum pads 56x73 microns at 65 micron pitch.





# Curve Description



Large distribution of standard

10 mV current, two probes, trace resistance not subtracted.

# Probe Tip Profile: Smooth vs Rough

0.3 micron clean

3.0 micron clean



Both probes nominal 1.0 mil diameter. Smooth tip profile produces lower contact area but much more consistent and easier to observe.

Contact Resistance Mechanisms

# Probe cards

- 0.8 mil diameter tip
- 3 tiers
- tungsten-rhenium
- 1.5 gm/mil OT probe force

- 1.0 mil diameter tip
- 3 tiers
- tungsten-rhenium
- 1.2 gm/mil OT probe force

## About Contamination





## Baseline Contact Resistance

Z-Only Clean



Contact Resistance Mechanisms





Wafer 20, PC 3

Contact Resistance Mechanisms



Matrix Plot of PR V Data



Contact Resistance Mechanisms

## waferWoRx Data

Matrix Plot of Scrub Data 1000 1500 0 500 0,4 0,6 0,8 1,0 1,2 1,4 15 25 35 5 -300 200 Pad 100 -0 1500 1000 Sequence 500 0. -2.0-1.5 scrub.area -1.0 . 1 -0.5 1.4 1.2\*\*\*\*\*\*\* \*\*\*\*\*\*\*\*\* 1.0 scrub.minor \*\*\*\*\*\*\*\* 0.8 ----..... 0.6 0.4 -2.10 1.85 -1.60scrub.major -1.35 ÷ -1.10 -0.85 35 25 pad.damage .;**i**]] 15 5-0.5 1.5 0.85 1.10 1.35 1.60 1.85 2.10 1.0 2.0 ó 100 200 300



Matrix Plot of Independent Variables



## Scrub



Contact Resistance Mechanisms



## Spread of Resistance by Tier



Contact Resistance Mechanisms

# Tip Diameter



Contact Resistance Mechanisms

## Calculated Pressure



Contact Resistance vs Estimated Pressure

Contact Resistance Mechanisms

## Contact Calculations

Carbonero et al

Probe resistance is the sum of effects due to constriction and contamination,

$$R_{tot} = R_{constriction} + R_{contamination} = \frac{\rho_{probe} + \rho_{pad}}{4na} + \frac{\sigma}{A} \quad (1)$$
If the area considered is covered with resistive film we have  $A = n\pi a^2$  and  $R_{tot} = \frac{\rho_{probe} + \rho_{pad}}{4na} + \frac{\rho_{film}l_{thickness}}{n\pi a^2}$ .  
(2)  
Assuming  $R_{constriction} = \text{Constant}$  and  
 $R_{constiction} << R_{contamination}$  the contact resistance is dictated by the thickness of the film and the radius of t

the "A-spots",  $R_{tot} \cong \frac{\rho_{\text{film}} l_{\text{thickness}}}{n \pi a^2}$ . (3)

Actually, the tip is not a homogenous surface so

 $R_{tot} \cong \sum_{i} \frac{\rho_{i} l_{i}}{\pi a_{i}^{2}}$ , but that's not very useful.

Contact resistance should vary with the film thickness and inversely with the contact area.

# Scrub Profiles: Where is that contact area?



## Probe Tip Profile: Contact Zones

Toe: leading edge, free of adhered metal, film contamination

Crown: lowest before probing, highest pressure, adhered metal, film contamination



Low level of contamination on wafers

Heel: trailing edge, some adhered metal, particulate contamination

## Probe Tip Profile: Contact Zones

Toe: leading edge, free of adhered metal, film contamination

Crown: lowest before probing, highest pressure, adhered metal, film contamination



High level of known contamination on wafers

Heel: trailing edge, some adhered metal, particulate contamination

Shape, size and placement vary depending on tip diameter, tip profile, probe tier and pad contamination

## Probe Tip Profile: Contact Zones



## Probe Tip Profile: Force Directions



## Summary

- Contact resistance due to contamination is much greater that innate probe resistance.
- Probe diameter is most important to low contact resistance due to influence on contact area.
- Force required may be just enough to break the oxide layer, produce good contact and maintain self cleaning. After breaking oxide more force may not necessarily reduce contact resistance.
- Primary conductive area may be crown of probe in steady conditions.